

Failed

Saved

(253) 313/2.1

(9681) (drain or source or gate) adj contact

(2448) vertical adj (MOS or FET or MOSFET or transistor)

(467) ((drain or source or gate) adj contact) and (vertical adj (MOS or FET or MOSFET or transis...

(76267) 438/5

(94201) 438/5

(1179) (vertical adj (MOS or FET or MOSFET or transistor)) and 438/5

(248) (((drain or source or gate) adj contact) and (vertical adj (MOS or FET or MOSFET or transi...

(1) 09/740113

(1) 09/740113 and borderless

(14131) capacitor and memory and (fet (field near effect near transistor) (field-effect near tra...

(12) (capacitor and memory and (fet (field near effect near transistor) (field-effect near trans...

(345) gate with (damascene near5 (method process))

(17) (capacitor and memory and (fet (field near effect near transistor) (field-effect near trans...

(7) ((capacitor and memory and (fet (field near effect near transistor) (field-effect near trans...

(1) 09/740113 and insulating

(1) 09/740113 and semiconductor near body

(1) 09/740113 and gate near contact

(10779) collar near (portion layer)

(74488) (fet (field near effect near transistor) (field-effect near transistor))

(77) (collar near (portion layer)) and ((fet (field near effect near transistor) (field-effect n...

(47) ((collar near (portion layer)) and ((fet (field near effect near transistor) (field-effect...

(1) 09/740113 and first near conductor

(1) 09/740113 and second near conductor

(1) 6441422.pn.

(367) (collar near (portion layer)) and capacitor

(264) ((collar near (portion layer)) and capacitor) and (@ad<20001219 @rlad<20001219)

(65479) transistor with (MOS or FET or DRAM or IGFET)

(6939) (transistor with (MOS or FET or DRAM or IGFET)) with insulat\$4 with gate

(1616) 438/197

(6503) ((transistor with (MOS or FET or DRAM or IGFET)) with insulat\$4 with gate) and ((drain an...

(125) (((transistor with (MOS or FET or DRAM or IGFET)) with insulat\$4 with gate) and ((drain an...

(165) (((transistor with (MOS or FET or DRAM or IGFET)) with insulat\$4 with gate) and ((drain an...

(26) (((transistor with (MOS or FET or DRAM or IGFET)) with insulat\$4 with gate) and ((drain an...

40 not 32

USPAT:US:PGPUB,EPC:JPO

Default operator: OR

Highlight all hit items only

40 not 32

BRG term ISAR term Image Text HTML

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U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	3	Im
1	<input type="checkbox"/>	US 20040048435 A1	20040311	29	Method of forming MOS transistor	438/239	438/275		Kim, Myoung-soo	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
2	<input type="checkbox"/>	US 20030134464 A1	20030717	55	Semiconductor device and method for the manufacture	438/239	257/E21.009; 257/E21.576;		Hidaka, Osamu et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
3	<input type="checkbox"/>	US 20020142540 A1	20021003	14	Method of manufacturing semiconductor integrated	438/239	438/241		Katayama, Satoshi	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
4	<input type="checkbox"/>	US 20020009847 A1	20020124	21	SEMICONDUCTOR DEVICE, AND MANUFACTURING METHOD OF THE	438/239	257/296; 257/E21.011;		WATANABE, AKIYOSHI	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
5	<input type="checkbox"/>	US 20010012698 A1	20010809	29	Metal oxide thin films for high dielectric constant	438/782	257/E21.272; 257/E27.016;		Hayashi, Shinichiro et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
6	<input type="checkbox"/>	US 20010005610 A1	20010628	12	Semiconductor device having metal silicide film and	438/239	257/E21.166; 257/E21.296;		Fukase, Tadashi et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US

Ready

NUM

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L1: (8) ("3883410" | "4115960" | "4968397" | "5733799" | "5753096" | "6165819" | "6376888" | "64...

L2: (0) 6727129.URPN.

L7: (7057) ((transistor with (MOS or FET or DRAM or IGPET)) with insulat\$4 with gate) and ((drai...

L9: (2118) 438/238

L10: (92) 7 and 9

L11: (1858) 438/239

L12: (74) 11 and 7

L13: (51) 12 not 10

L14: (1108) 438/243

L15: (46) 14 and 7

L16: (43) 15 not 13

L17: (37) 16 not 10

L18: (942) 438/268

L19: (1377) 438/633

L20: (13) 7 and 19

L21: (11) 20 not 17

L22: (104) 7 and 18

L23: (99) 22 not 10

L24: (96) 23 not 17

L25: (94) 24 not 13

L26: (6) ("5382816" | "5480838" | "5689127" | "5780327" | "6396108" | "6506638").PN.

L27: (1) ("6441442").PN.

L28: (1685) (438/270).CCLs.

L29: (72) 7 and 28

L30: (47) 29 not 25

L31: (45) 30 not 10

L32: (41) 31 not 17

L33: (196) 438/272

L34: (15) 7 and 33

L35: (13) 34 not 32

L36: (1858) 438/239

L37: (74) 36 and 7

L38: (51) 37 not 10

L39: (51) 38 not 17

L40: (51) 39 not 25

L41: (51) 40 not 32

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DRS term

ISAR term

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	U	A	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	S	I	US	
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2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030134464A1	20030717	55	Semiconductor device and method for the manufacture	438/239	257/E21.009; 257/E21.576;		Hidaka, Osamu et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020142540A1	20021003	14	Method of manufacturing semiconductor integrated	438/239	438/241		Katayama, Satoshi	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020009847A1	20020124	21	SEMICONDUCTOR DEVICE, AND MANUFACTURING METHOD OF THE	438/239	257/296; 257/E21.011;		WATANABE, AKIYOSHI	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20010012698A1	20010809	29	Metal oxide thin films for high dielectric constant	438/782	257/E21.272; 257/E27.016;		Hayashi, Shinichiro et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20010005610A1	20010628	12	Semiconductor device having metal silicide film and	438/239	257/E21.166; 257/E21.296;		Fukase, Tadashi et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US

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Details

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DB1 USPAT, US-PCPUB, EPO, JPO

Default operator: OR

Highlight all hit terms exactly

BRB term RDR term Image Text HTML

status Text Retrieval Image Retrieval Errors Error Definition type Search Text DBs

Ready

NUM

Drafts

BRS:

Pending

Active

L1: (2858) ((transistor with (MOS or FET or DRAM or IGPET)) with insulatS4 with gate) with (d

L2: (1269) 438/275

L3: (54) 1 and 2

L4: (653) 438/279

L5: (22) 4 and 1

Failed

Saved

(9681) (drain or source or gate) adj contact

(2448) vertical adj (MOS or FET or MOSFET or transistor)

(467) ((drain or source or gate) adj contact) and (vertical adj (MOS or FET or MOSFET or tran